

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"6,115,828".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:06
S2	13	"689422"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:13
S3	1724	(714/6).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:14
S4	887	(714/5).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:14
S5	615	(714/7).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:14
S6	2907	S3 or S4 or S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:14
S7	33783	compar\$3 with (fault\$3 or fail\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:15
S8	1353	compar\$3 with address with (fault\$3 or fail\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:15
S9	34	S8 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:15

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S10	408	(714/8).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:14
S11	9	S8 and S10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:14
S12	38	S9 or S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:14
S13	633	column with row with address with (fault\$3 or fail\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:18
S14	3188	S6 or S10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:18
S15	31	S13 and S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:19
S16	17	S15 not S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:59
S17	113015	semiconductor adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:22
S18	400	S14 and S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 14:22

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S19	10	(US-20040153843-\$ or US-20050160310-\$).did. or (US-6115828-\$ or US-6408401-\$ or US-6041422-\$ or US-6397349-\$ or US-5938774-\$ or US-6785837-\$ or US-6505305-\$ or US-6571353-\$). did.	US-PGPUB; USPAT	OR	ON	2006/04/07 15:27
S20	6	S19 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 15:27
S21	8	S19 and column and row	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 15:27
S22	5	S20 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 15:59
S23	51	("3222653" "3311887" "3331058" "3422402" "3434116" "3633175" "3735368" "3753244" "4015126" "4250570" "4422161" "4426688" "4450559" "4523313" "4527251" "4532611" "4556975" "4584681" "4639897" "4656609" "4656610" "4744060" "4745582" "4783781" "4796233" "4817056" "4849938" "4849939" "4862416" "5195057" "5208782" "5243570" "5249156" "5297088" "5315551" "5329473" "5381370" "5416740" "5822779").PN. OR ("6041422"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/07 15:53
S24	55	S15 or S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 15:59
S25	438	S24 or S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 15:59

EAST Search History

S26	51	S25 and ("and" adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 16:09
S27	18	S23 and ("and" adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 16:01
S28	66	S26 or S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 16:00
S29	6813	(compar\$5 with row) and (compar\$5 with column)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 16:10
S30	32	S29 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 16:10
S31	10	(US-20050160310-\$ or US-20040153843-\$).did. or (US-6408401-\$ or US-6115828-\$ or US-6785837-\$ or US-5938774-\$ or US-6505305-\$ or US-6397349-\$ or US-6041422-\$ or US-6571353-\$). did.	US-PGPUB; USPAT	OR	ON	2006/04/10 10:15
S32	1	S31 and latch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:24
S33	1724	(714/6).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26
S34	887	(714/5).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26

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S35	615	(714/7).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26
S36	2907	S33 or S34 or S35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26
S37	408	(714/8).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26
S38	3188	S36 or S37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26
S39	6813	(compar\$5 with row) and (compar\$5 with column)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26
S40	44	S38 and S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:26
S41	113068	semiconductor adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:27
S42	400	S38 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:27
S43	22	S42 and S40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 10:27

EAST Search History

S44	29	("4459685" "4601019" "5179536" "5381370" "5422850" "5452251" "5513144" "5528539" "5548225" "5594693" "5604702" "5648934" "5684740" "5729551" "5751647" "5914907" "6038682").PN. OR ("6199177").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/10 11:48
S45	24	("4051354" "4380066" "5299202" "5416740" "5430678" "5812467" "5889710" "5958065" "5969906").PN. OR ("6115828").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/10 11:45
S46	53	S44 or S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 11:48
S47	41	S46 and compar\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 12:32
S48	1232	(address near4 (fault\$3 or fail\$3)) with compar\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 13:06
S49	333	S41 and S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 13:05
S50	7	S49 and S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 13:05
S51	2514	(address near4 (fault\$3 or fail\$3 or defective)) with compar\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 13:06
S52	400	S38 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 13:07

EAST Search History

S53	31	S51 and S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S54	2	"4,389,715".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 13:27
S55	869	block same (row with compar\$5) same (column with compar\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S56	1724	(714/6).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S57	887	(714/5).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S58	615	(714/7).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S59	2907	S56 or S57 or S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S60	408	(714/8).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S61	3188	S59 or S60	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S62	113068	semiconductor adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24

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S63	400	S61 and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S64	10	S55 and S63	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/10 16:24
S65	12	(US-20040153843-\$ or US-20050160310-\$).did. or (US-6115828-\$ or US-6199177-\$ or US-6505305-\$ or US-6408401-\$ or US-6397349-\$ or US-6785837-\$ or US-5938774-\$ or US-6041422-\$ or US-6571353-\$ or US-4389715-\$). did.	US-PGPUB; USPAT	OR	ON	2006/04/12 09:58
S66	2	S65 and latch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/12 09:47
S67	9	(compar\$5 with (cell or block)) and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/12 10:13
S68	6	(compar\$5 with array) and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/12 10:13



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